W hat is claimed is:

1. An apparatus, comprising:

a voltage source to provide a substantially temperature stable output voltage;

a first semiconductor device biased by the substantially temperature stable output voltage to provide a first output current; and

a second semiconductor device biased by the substantially temperature stable output voltage to provide a second output current, the second semiconductor device to couple to the first semiconductor device to provide a reference current approximately equal to a difference between the first and the second output currents.

2. The apparatus of claim 1, wherein the first and the second semiconductor devices are biased by the substantially temperature stable output voltage to operate in a saturation mode.

3. The apparatus of claim 1, wherein the first and the second semiconductor devices are fabricated on a single die.

4. The apparatus of claim 1, further including:

a differencing circuit to couple to the first and the second semiconductor devices.

5. The apparatus of claim 1, further including:

a pair of current mirrors to couple to the first and the second semiconductor devices.

6. The apparatus of claim 5, wherein the first and the second semiconductor devices and the pair of current mirrors are fabricated on a single die.

7. The apparatus of claim 1, wherein a reference magnitude of the reference current is approximately equal to a difference between the second output current and a product of the first output current and a scaling constant.

8. The apparatus of claim 7, further comprising:

a differencing circuit including a first current mirror selected to determine the scaling constant.

9. The integrated circuit of claim 9, wherein the voltage source comprises a band-gap voltage source.

10. An integrated circuit, comprising:

a voltage source to provide a substantially temperature stable output voltage;

a first semiconductor device biased by the substantially temperature stable output voltage to provide a first output current; and

a second semiconductor device biased by the substantially temperature stable output voltage to provide a second output current, the second semiconductor device to couple to the first semiconductor device to provide a reference current approximately equal to a difference between the first and the second output currents; and

an output node in electrical communication with the first and second semiconductor devices to carry the reference current.

11. The integrated circuit of claim 10, wherein the first and the second semiconductor devices are biased by the substantially temperature stable output voltage to operate in a saturation mode.

12. The integrated circuit of claim 10, further including:

a differencing circuit to couple to the first and the second semiconductor devices.

13. The integrated circuit of claim 12, wherein the reference current has a reference magnitude approximately equal to the difference between the second output current and a product of the first output current and a scaling constant determined by a current mirror included in the differencing circuit.

14. The integrated circuit of claim 10, wherein each one of the first and the second semiconductor devices comprise a field effect transistor.

15. The integrated circuit of claim 14, further including:

a pair of current mirrors to couple to the first and the second semiconductor devices, wherein each one of the pair of current mirrors includes a pair of field effect transistors, and wherein the first and the second semiconductor devices and the pair of current mirrors are fabricated on a single die.

16. The integrated circuit of claim 10, wherein the voltage source comprises a band-gap voltage source.

17. A system, comprising:

a cellular telephone including a voltage source to provide a substantially temperature stable output voltage, a first semiconductor device biased by the substantially temperature stable output voltage to provide a first output current, and a second semiconductor device biased by the substantially temperature stable output voltage to provide a second output current, the second semiconductor device to couple to the first semiconductor device to provide a reference current approximately equal to a difference between the first and the second output currents.

18. The system of claim 17, further comprising a differencing circuit to couple to the first and the second semiconductor devices.

19. The system of claim 18, wherein the differencing circuit includes a first current mirror selected to determine a scaling constant.

20. The system of claim 19, wherein the reference current has a reference magnitude approximately equal to the difference between the second output current and a product of the first output current and the scaling constant.